EAST Search History *(13 pp.)*

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	jp-2001015798$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:16
L2	2	jp-2002232005$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:17
L3	2	jp-2000174344$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:20
L4	2	("6350997").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:21
L5	2	jp-11307810$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:21
L6	2	jp-2002344017$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:53
L7	2	("20020104997").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:53
L8	0	7 and doped near12 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:53
L9	0	7 and undoped near12 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:53

L10	0	7 and un-doped near12 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:54
L11	0	7 and un-doped near12 MQW	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:54
L12	0	7 and undoped near12 MQW	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:54
L13	0	7 and doped near12 MQW	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:54
L14	14398	((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/43.01) or (372/45.01)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 15:44
L15	0	14 and exfoliat$3.ti,ab,clm. and (spacer barrier).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:45
L16	1511	14 and (spacer barrier).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:45
L17	509	14 and (spacer barrier).ti,ab,clm. and (clad cladding).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:46
L18	12	14 and (spacer barrier).ti,ab,clm. and (clad cladding).ti,ab,clm. and (hitachi.as. konno.in.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:47
L19	10	14 and (spacer barrier).clm. and (clad cladding).clm. and (hitachi.as. konno.in.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:47

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S1	5	"807413".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 18:43
S2	2	jp-2002226846$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 19:06
S3	41	exfoliati$2.ti,ab,clm. and (light-emitting adj (device diode) light adj emitting adj (device diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:12
S4	3	exfoliati$2.ti,ab,clm. and (light-emitting adj (device diode) light adj emitting adj (device diode)) and AlGaAs and (ITO indium-tin-oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:20
S5	1	exfoliati$2 near6 AlGaAs and (ITO indium-tin-oxide) and (257/79. ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:22
S6	1	exfoliati$2 near6 AlGaAs and (ITO indium-tin-oxide) and (372/4$1. ccls. 372/50.ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:22
S7	2	(lift-off exfoliati$2) near6 AlGaAs and (ITO indium-tin-oxide) and (372/4$1.ccls. 372/50.ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:24
S8	5	(lift-off exfoliati$2) near6 (aluminum AlGaAs) and (ITO indium-tin-oxide) and (372/4$1. ccls. 372/50.ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:26
S9	1	(exfoliati$2) near6 (aluminum AlGaAs)and (372/4$1.ccls. 372/50. ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:26

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S10	1	(exfoliati$2) near6 (aluminum AlGaAs) and (372/4$1.ccls. 372/50.ccls. 257/79.ccls. 257/8$1. ccls. 257/9$1.ccls. 257/10$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:26
S11	1	(exfoliati$2) near6 (aluminum AlGaAs Al AlAs) and (372/4$1.ccls. 372/50.ccls. 257/79.ccls. 257/8$1. ccls. 257/9$1.ccls. 257/10$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:27
S12	131	(exfoliati$2) near6 aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:29
S13	68	(exfoliati$2) near3 aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:34
S14	19	(ITO indium-tin-oxide) near6 (AlGaAs AlAs) and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:03
S15	1259	stop adj layer.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:49
S16	2	stop adj layer.ti. and light-emitting adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:49
S17	0	(ITO indium-tin-oxide) near6 (AlGaAs:Zn AlGaAs:Si AlGaAs:Ge AlAs:Zn AlAs:Si AlGa:Ge) and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:04
S18	0	(ITO indium-tin-oxide) near6 ("AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:04

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S19	0	(ITO indium-tin-oxide) near6 (AlGaAs near4 ((heavily highly) adj doped) "AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:05
S20	0	(ITO indium-tin-oxide) near10 (AlGaAs near4 ((heavily highly) adj doped) "AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:06
S21	17	(ITO indium-tin-oxide) near10 AlGaAs and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:06
S22	0	(ITO indium-tin-oxide) near10 AlGaAs:Zn and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:06
S23	1	(ITO indium-tin-oxide) near10 AlGaAs near10 Zn and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:07
S24	1	(ITO indium-tin-oxide) near10 AlGaAs near10 (Si Ge Zn Mg Cd) and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:08
S25	0	(ITO indium-tin-oxide) near10 AlGaAs near10 heavily adj doped and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:08
S26	0	(ITO indium-tin-oxide) near10 AlGaAs near10 (n+ "N+" heavily adj doped) and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:09
S27	0	(ITO indium-tin-oxide) near10 AlGaAs near10 ("n.sub.+" "N.sub.+" heavily adj doped) and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:09

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S28	17	(ITO indium-tin-oxide) near10 AlGaAs and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:20
S29	4	ohmic adj contact near10 (AlAs AlGaAs) near10 (ITO TCO transparent) and (light-emitting adj diode light adj emitting adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:25
S30	2	ohmic adj contact near10 (AlAs AlGaAs) near10 (electrode) and (light-emitting adj diode light adj emitting adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:30
S31	0	ohmic adj contact near10 (AlAs AlGaAs) near10 (ITO TCO)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:31
S32	0	ohmic adj contact near10 (AlAs AlGaAs) near10 zinc adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:31
S33	106	ohmic adj contact near5 (AlAs AlGaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:32
S34	51	ohmic adj contact near3 (AlAs AlGaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:51
S35	0	ohmic adj contact near3 (AlAs AlGaAs) and exfoliat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:43
S36	0	(adhesion adhesive) near10 (AlAs AlGaAs) near10 ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:51
S37	5	ohmic adj contact near3 (AlAs AlGaAs) and "10.sup.19"$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:27

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S38	53	band adj gap near4 ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:54
S39	27	band adj gap near3 ITO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:47
S40	0	direct adj gap near3 ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:49
S41	0	direct adj gap near3 contact adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:50
S42	0	direct adj2 gap near3 contact adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:50
S43	6	contact adj resistance near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:00
S44	0	(p-type adj ito) near5 (band adj gap)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:06
S45	0	"Al.sub."$4"Ga.sub."$4As near10 band adj gap near10 (contact adj region ohmic adj contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:15
S46	2	"6236065".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:35
S47	2	"6495862".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:35

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S48	0	"6495862".pn. and AlGaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:35
S49	1	"6495862".pn. and exfoliat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:37
S50	1	"6495862".pn. and exfoliat$3 and (AlGaAs AlGaN Al aluminum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:50
S51	690	contact adj (region layer) near6 (impurity adj concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:51
S52	22	contact adj (region layer) near4 (impurity adj concentration) and transparent adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:51
S53	0	direct adj2 band adj gap near10 (ohmic adj contact contact adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/31 06:43
S54	6	"Al.sub."$4"Ga.sub."$4As near10 (ohmic adj contact contact adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/31 06:43
S55	10	(US-20020096688-$ or US-20020110940-$ or US-20040197981-$ or US-20040227151-$).did. or (US-5770489-$ or US-6055262-$ or US-6856087-$ or US-6867426-$).did. or (JP-2002226846-$).did. or (JP-2002226846-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/31 07:31
S56	3	S55 and Zn	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:19

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S57	2	S55 and Mg	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:20
S58	9	"6495862"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:21
S59	2	("6495862").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:21
S60	11	(US-20020096688-$ or US-20020110940-$ or US-20040197981-$ or US-20040227151-$).did. or (US-5770489-$ or US-6055262-$ or US-6856087-$ or US-6867426-$ or US-6495862-$).did. or (JP-2002226846-$).did. or (JP-2002226846-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/31 07:31
S61	1	S60 and autodoped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:33
S62	75	autodoped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:33
S63	35	autodoped.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:33
S64	20	jp-1130810$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/01 15:09
S65	2	jp-11307810$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/01 15:09

S66	2	jp-2002344017$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/01 15:10
S67	2	("6350997").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/01 15:10
S68	2	"6350997".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 16:28
S69	3	"116324".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 09:42
S70	1	(US-20040227151-$).did.	US-PGPUB	OR	OFF	2005/11/13 18:03
S71	1	S70 and prevent$3 near6 concentrat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/13 18:06
S72	2	("5869849").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/13 18:10
S73	8	JP-2002232005$-$.did. JP-2000174344$-$.did. JP-08097467$-$.did. JP-2000312028$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 18:38
S74	2	jp-2003158887$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:11
S75	418	graded near3 clad$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/13 19:34

S76	6	(double graded) near3 clad$4 and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:42
S77	10	(double graded) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:54
S78	10	(double graded bi-layer) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:54
S79	16	(double graded bi-layer laminate) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:55
S80	3	(double graded bi-layer laminate) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3 and AlGaInP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 20:29
S81	0	"5869849".pn. and (mqw multiple ad adj "well")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 20:30
S82	1854	(AlGaInP GaAlInP InGaAlP InAlGaP) and (mqw multiple ad adj "well")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 20:31
S83	348	(AlGaInP GaAlInP InGaAlP InAlGaP) with (mqw multiple ad adj "well")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 20:31
S84	29	(AlGaInP GaAlInP InGaAlP InAlGaP) with (mqw multiple ad adj "well") and ito	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 20:31
S85	6	(AlGaInP GaAlInP InGaAlP InAlGaP) with (mqw multiple ad adj "well") and ito and (zn zinc) near3 dop$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:03

S86	134	(mqw multiple ad adj "well") with quantum adj2 efficiency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:04
S87	0	(mqw multiple ad adj "well") with quantum adj2 efficiency with light-emitting adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:04
S88	14	(mqw multiple ad adj "well") with quantum adj2 efficiency with (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:05
S89	3	(mqw multiple adj "well") with quantum adj2 efficiency with (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:05
S90	4	(mqw multiple adj quantum adj "well") with quantum adj2 efficiency with (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:05
S91	117	MQW near6 efficiency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 08:58
S92	0	MQW near6 efficiency near6 light adj emitting and LED.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 08:58
S93	7	MQW near6 efficiency near6 light adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 08:58
S94	20	MQW near6 efficiency near6 ("LED" light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 09:49
S95	11454	((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 09:49

EAST Search History

S96	12220	((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/43.01)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 09:49
S97	124	S96 and (damag$3 exfoliat$3 degradat$3 erosion eroding corrosion corroding) near6 electrode and transparent near4 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 09:52
S98	83	S96 and (damag$3 exfoliat$3 degradat$3 erosion eroding corrosion corroding) near6 electrode and transparent near4 electrode and @ad<"20030401"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 09:52
S99	1	(US-20040227151-$).did.	US-PGPUB	OR	OFF	2006/01/26 16:21
S10 0	1	(US-20040227151-$).did. and "between" and (band adj gap gap)	US-PGPUB	OR	OFF	2006/01/26 16:22
S10 1	2	("5869849").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 12:02
S10 2	2	("20020104997").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 12:14
S10 3	81	waveguide adj layer near6 (clad cladding) and (257/8$1.ccls. 257/9$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 12:18
S10 4	4	(AlGaInP AlInGaP) and (257/8$1. ccls. 257/9$1.ccls.) and "undoped" near4 "between" near4 (clad cladding) near4 active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:14